TEMIC

Siliconix

2N/PN/SST4391 Series

N-Channel JFETs

2N4391 PN4391 SST4391
2N4392 PN4392 SST4392
2N4393 PN4393 SST4393

Product Summary

Part Number	$V_{GS(off)}$ (V)	$r_{DS(on)}$ Max (Ω)	$I_{D(off)}$ Typ (pA)	t_{ON} Typ (ns)
2N/PN/SST4391	−4 to −10	30	5	4
2N/PN/SST4392	−2 to −5	60	5	4
2N/PN/SST4393	−0.5 to −3	100	5	4

2N4391, For applications information see AN104, page 21.
PN/SST4393, For applications information see AN106, page 28.

Features

- Low On-Resistance: 4391<30 Ω
- Fast Switching—t_{ON}: 4 ns
- High Off-Isolation: $I_{D(off)}$ with Low Leakage
- Low Capacitance: < 3.5 pF
- Low Insertion Loss

Benefits

- Low Error Voltage
- High-Speed Analog Circuit Performance
- Negligible "Off-Error," Excellent Accuracy
- Good Frequency Response, Low Glitches
- Eliminates Additional Buffering

Applications

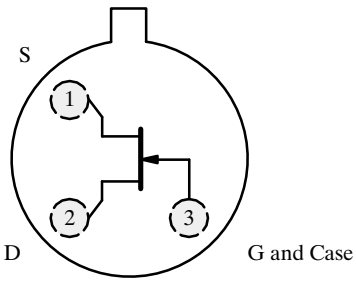
- Analog Switches
- Choppers
- Sample-and-Hold
- Normally "On" Switches
- Current Limiters
- Commutators

Description

The 2N/PN/SST4391 series features many of the superior characteristics of JFETs which make it a good choice for demanding analog switching applications and for specialized amplifier circuits.

The 2N series hermetically-sealed TO-206AA (TO-18) can is available with processing per MIL-S-19500 (see Military Information). Both the PN, TO-226AA (TO-92), and SST, TO-236 (SOT-23), series are available in tape-and-reel for automated assembly (see Packaging Information). For similar dual products, see the 2N5564/5565/5566 data sheet.

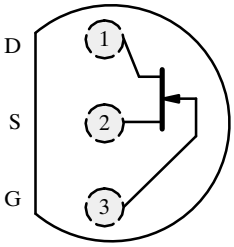
TO-206AA
(TO-18)



Top View

2N4391
2N4392
2N4393

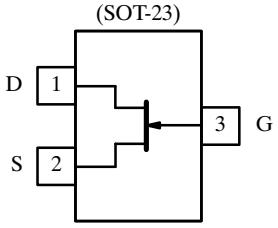
TO-226AA
(TO-92)



Top View

PN4391
PN4392
PN4393

TO-236
(SOT-23)



Top View

SST4391 (CA)*
SST4392 (CB)*
SST4393 (CC)*

*Marking Code for TO-236

2N/PN/SST4391 Series

Absolute Maximum Ratings

Gate-Drain, Gate-Source Voltage: (2N/PN Prefixes) . . . . . −40 V
(SST Prefix) . . . . . −35 V

Gate Current . . . . . 50 mA

Lead Temperature . . . . . 300 °C

Storage Temperature : (2N Prefix) . . . . . −65 to 200 °C
(PN/SST Prefixes) . . . . . −55 to 150 °C

Operating Junction Temperature : (2N Prefix) . . . . . −55 to 200 °C
(PN/SST Prefixes) −55 to 150 °C

Power Dissipation : (2N Prefix)[a] . . . . . (T_C = 25°C) 1800 mW
(PN/SST Prefixes)[b] . . . . . 350 mW

Notes
a. Derate 10 mW/°C above 25°C
b. Derate 2.8 mW/°C above 25°C

Specifications[a]

Parameter	Symbol	Test Conditions		Typ[b]	Limits 4391 Min	Limits 4391 Max	Limits 4392 Min	Limits 4392 Max	Limits 4393 Min	Limits 4393 Max	Unit
Static											
Gate-Source Breakdown Voltage	$V_{(BR)GSS}$	I_G = −1 μA, V_{DS} = 0 V	2N/PN	−55	−40		−40		−40		V
			SST	−55	−35		−35		−35		
Gate-Source Cutoff Voltage	$V_{GS(off)}$	V_{DS} = 20 V	2N/PN: I_D = 1 nA		−4	−10	−2	−5	−0.5	−3	V
		V_{DS} = 15 V	SST: I_D = 10 nA								
Saturation Drain Current[c]	I_{DSS}	V_{DS} = 20 V, V_{GS} = 0 V	2N		50	150	25	75	5	30	mA
			PN		50	150	25	100	5	60	
			SST		50		25		5		
Gate Reverse Current	I_{GSS}	V_{GS} = −20 V, V_{DS} = 0 V	2N/SST	−5		−100		−100		−100	pA
			PN	−5		−1000		−1000		−1000	
			2N: T_A = 150°C	−13		−200		−200		−200	nA
			PN: T_A = 100°C	−1		−200		−200		−200	
			SST: T_A = 125°C	−3							
Gate Operating Current	I_G	V_{DG} = 15 V, I_D = 10 mA		−5							pA
Drain Cutoff Current	$I_{D(off)}$	V_{DS} = 20 V	2N: V_{GS} = −5 V	5						100	pA
			2N: V_{GS} = −7 V	5				100			
			2N: V_{GS} = −12 V	5		100					
			PN: V_{GS} = −5 V	0.005						1	nA
			PN: V_{GS} = −7 V	0.005				1			
			PN: V_{GS} = −12 V	0.005		1					
		SST V_{DS} = 10 V, V_{GS} = −10 V		5		100		100		100	pA
		V_{DS} = 20 V, T_A = 150°C	2N: V_{GS} = −5 V	13						200	nA
			2N: V_{GS} = −7 V	13				200			
			2N: V_{GS} = −12 V	13		200					
		V_{DS} = 20 V, T_A = 100°C	PN: V_{GS} = −5 V	1						200	
			PN: V_{GS} = −7 V	1				200			
			PN: V_{GS} = −12 V	1		200					
		V_{DS} = 10 V, T_A = 125°C	SST: V_{GS} = −10 V	3							
Drain-Source On-Voltage	$V_{DS(on)}$	V_{GS} = 0 V	I_D = 3 mA	0.25						0.4	V
			I_D = 6 mA	0.3				0.4			
			I_D = 12 mA	0.35		0.4					

Specifications[a]

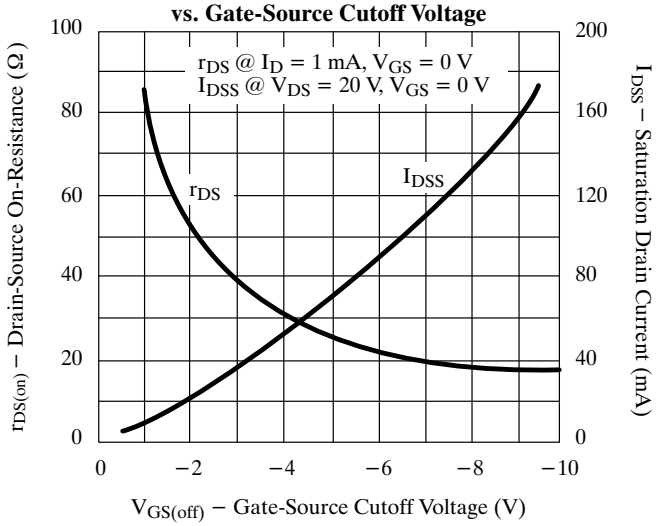
Parameter	Symbol	Test Conditions		Typ[b]	Limits 4391 Min	4391 Max	4392 Min	4392 Max	4393 Min	4393 Max	Unit
Static (Cont'd)											
Drain-Source On-Resistance	$r_{DS(on)}$	V_{GS} = 0 V, I_D = 1 mA				30		60		100	Ω
Gate-Source Forward Voltage	$V_{GS(F)}$	I_G = 1 mA, V_{DS} = 0 V	2N	0.7		1		1		1	V
			PN/SST	0.7							
Dynamic											
Common-Source Forward Transconductance	g_{fs}	V_{DS} = 20 V, I_D = 1 mA, f = 1 kHz		6							mS
Common-Source Output Conductance	g_{os}			2 5							µS
Drain-Source On-Resistance	$r_{DS(on)}$	V_{GS} = 0 V, I_D = 0 mA , f = 1 kHz				30		60		100	Ω
Common-Source Input Capacitance	C_{iss}	V_{DS} = 20 V, V_{GS} = 0 V, f = 1 MHz	2N	12		14		14		14	pF
			PN	12		16		16		16	
			SST	13							
Common-Source Reverse Transfer Capacitance	C_{rss}	V_{DS} = 0 V, f = 1 MHz	2N: V_{GS} = −5 V	3.3						3.5	
			2N: V_{GS} = −7 V	3.2				3.5			
			2N: V_{GS} = −12 V	2.8		3.5					
			PN: V_{GS} = −5 V	3.5						5	
			PN: V_{GS} = −7 V	3.4				5			
			PN: V_{GS} = −12 V	3.0		5					
			SST: V_{GS} = −5 V	3.6							
			SST: V_{GS} = −7 V	3.5							
			SST: V_{GS} = −12 V	3.1							
Equivalent Input Noise Voltage	$\bar{e}_n$	V_{DS} = 10 V, I_D = 10 mA, f = 1 kHz		3							nV/√Hz
Switching											
Turn-On Time	$t_{d(on)}$	V_{DD} = 10 V, $V_{GS(H)}$ = 0 V, See Switching Circuit	2N/PN	2		15		15		15	ns
			SST	2							
	t_r		2N/PN	2		5		5		5	
			SST	2							
Turn-Off Time	$t_{d(off)}$		2N/PN	6		20		35		50	
			SST	6							
	t_f		2N/PN	13		15		20		30	
			SST	13							

Notes
a. T_A = 25°C unless otherwise noted. NCB
b. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.
c. Pulse test: PW ≤ 300 µs duty cycle ≤ 3%.

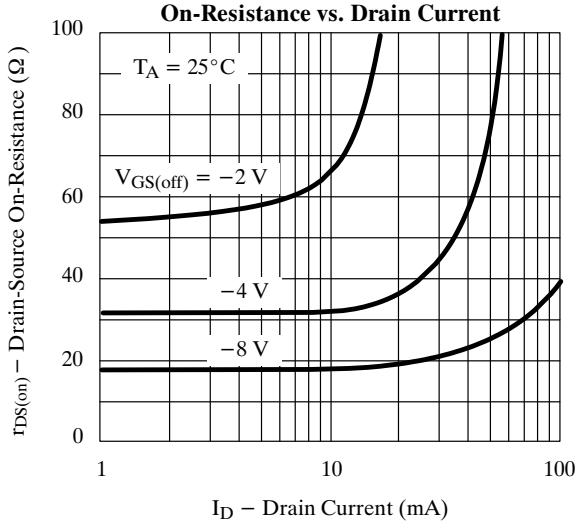
2N/PN/SST4391 Series

Typical Characteristics

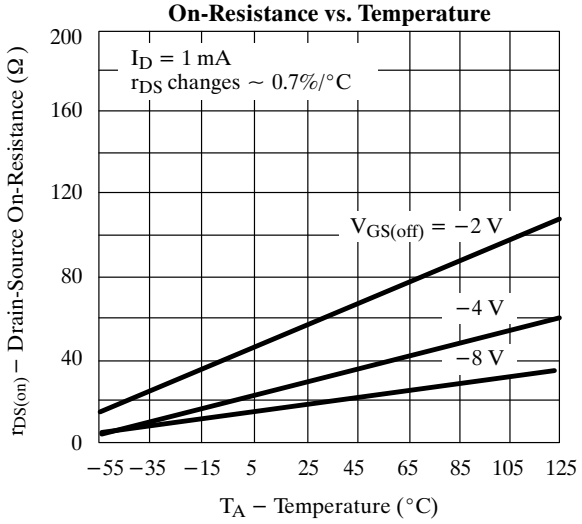
On-Resistance and Drain Current vs. Gate-Source Cutoff Voltage



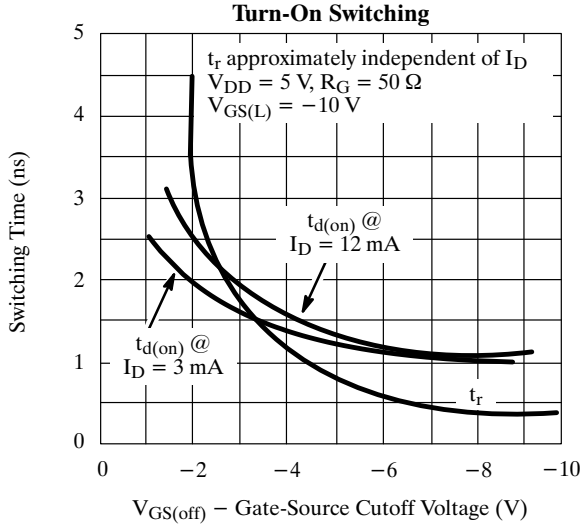
On-Resistance vs. Drain Current



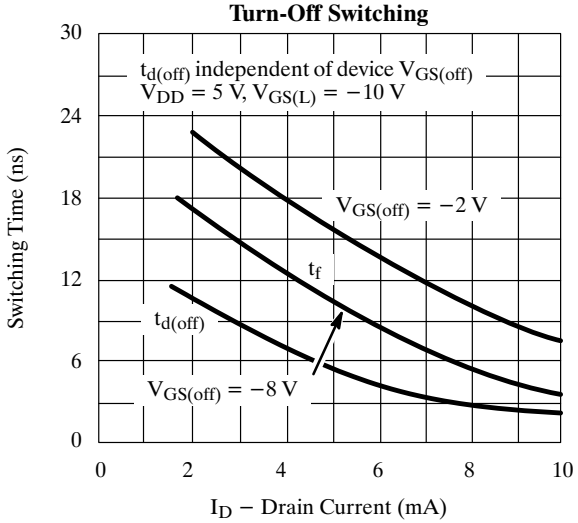
On-Resistance vs. Temperature



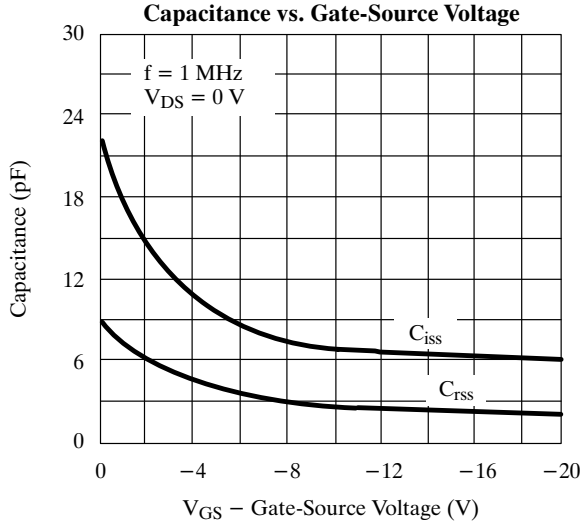
Turn-On Switching



Turn-Off Switching

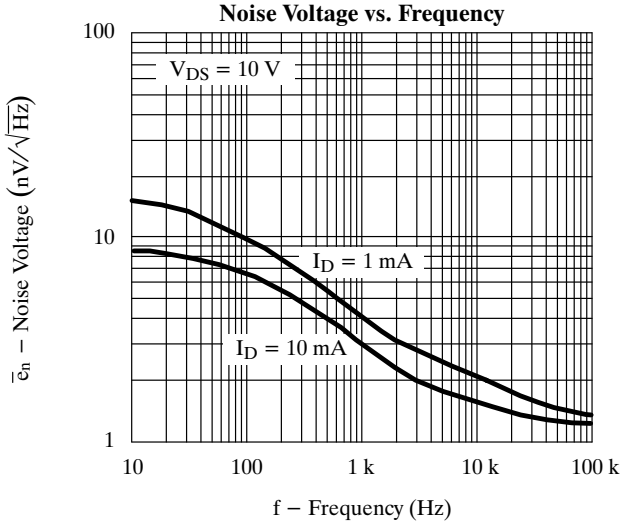


Capacitance vs. Gate-Source Voltage

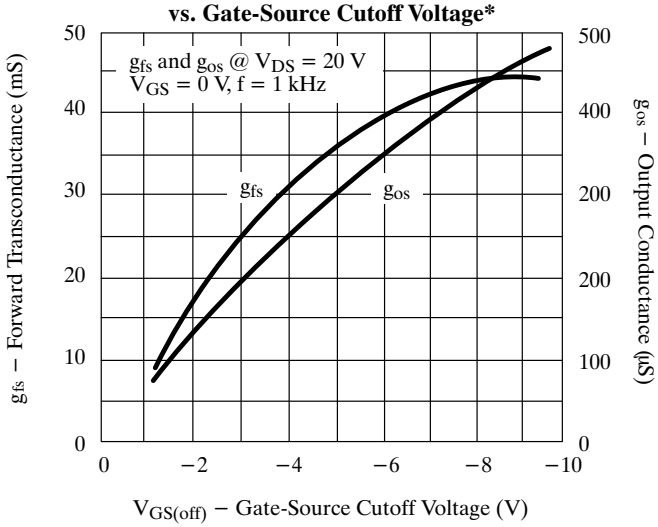


Typical Characteristics (Cont'd)

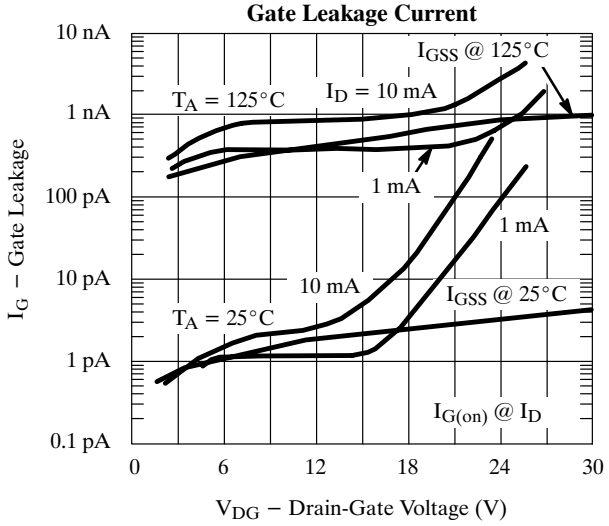
Noise Voltage vs. Frequency



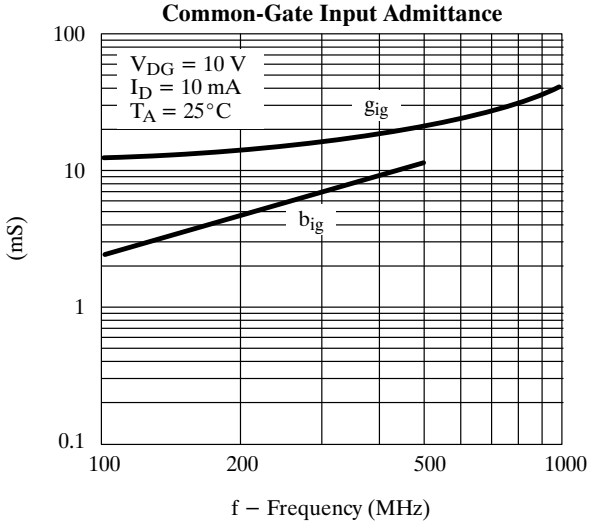
Forward Transconductance and Output onductance vs. Gate-Source Cutoff Voltage*



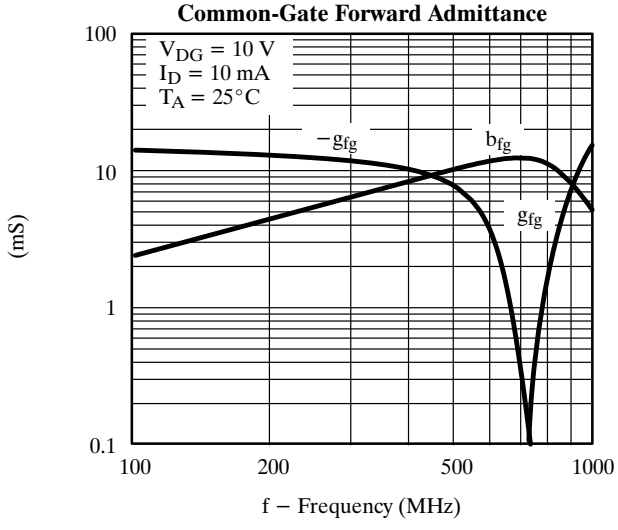
Gate Leakage Current



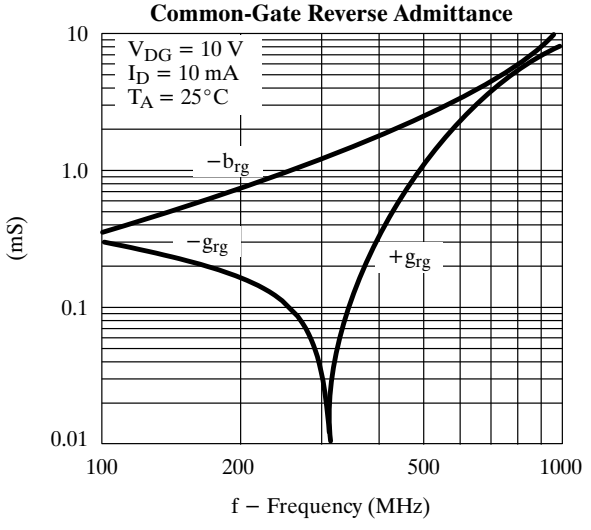
Common-Gate Input Admittance



Common-Gate Forward Admittance



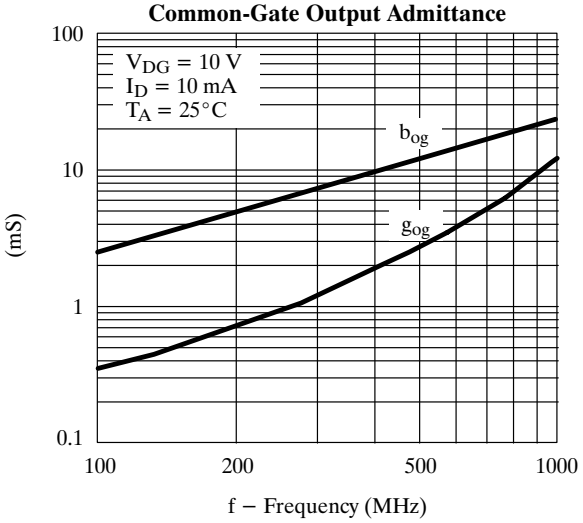
Common-Gate Reverse Admittance



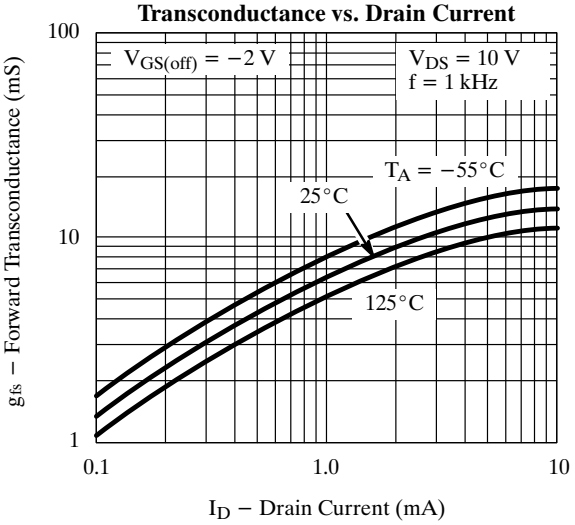
2N/PN/SST4391 Series

Typical Characteristics (Cont'd)

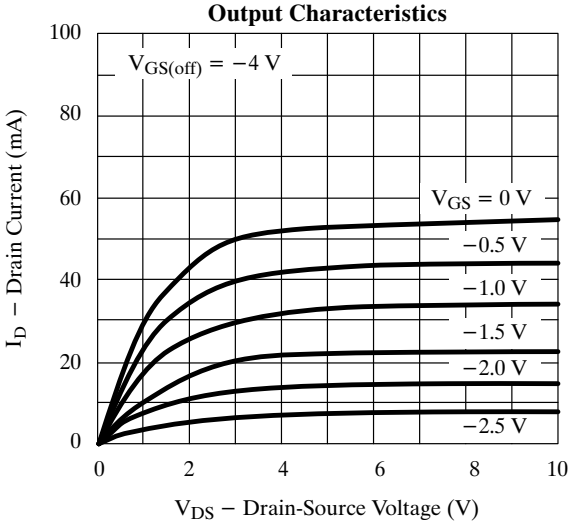
Common-Gate Output Admittance



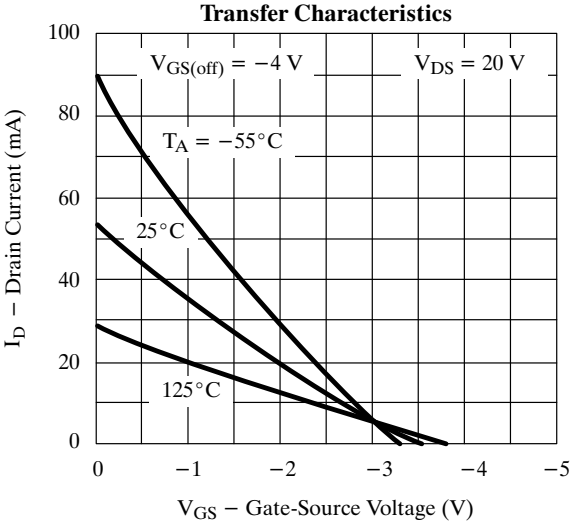
Transconductance vs. Drain Current



Output Characteristics



Transfer Characteristics



Switching Time Test Circuit

	4391	4392	4393
$V_{GS(L)}$	−12 V	−7 V	−5 V
R_L*	800 Ω	1600 Ω	3000 Ω
$I_{D(on)}$	12 mA	6 mA	3 mA

*Non-inductive

Input Pulse

Rise Time < 1 ns
Fall Time < 1 ns
Pulse Width 100 ns
PRF 1 MHz

Sampling Scope

Rise Time 0.4 ns
Input Resistance 10 MΩ
Input Capacitance 1.5 pF

See Typical Characteristics curves for changes.